

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,192,837 B2
APPLICATION NO. : 10/765027
DATED : March 20, 2007
INVENTOR(S) : Kwan Ju Koh

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

IN THE CLAIMS

Column 2, line 46 of the issued patent: change "forming a first oxide layer" to --forming a first oxide layer--.

Column 2, line 54 of the issued patent: change "including the tightly doped drain" to --including the lightly doped drain--.

Column 2, line 57 of the issued patent: change "second oxide layer aver an exposed portion" to --second oxide layer over an exposed portion--.

Column 2, line 62 of the issued patent: change "first aid do layer" to --first oxide layer--.

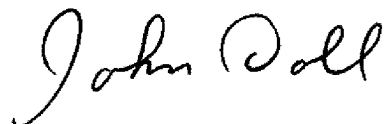
Column 3, lines 24-25 of the issued patent: change "etching to exposed substrate" to --etching the exposed substrate--.

Column 3, line 31 of the issued patent: change "removing to first nitride layer" to --removing the first nitride layer--.

Column 3, line 32 of the issued patent: change "to polysilicon layer" to --the polysilicon layer--.

Signed and Sealed this

Twenty-eighth Day of July, 2009



JOHN DOLL
Acting Director of the United States Patent and Trademark Office